MOSFETs Silicon P-Channel MOS (U-MOSVI)

# **TPCA8120**

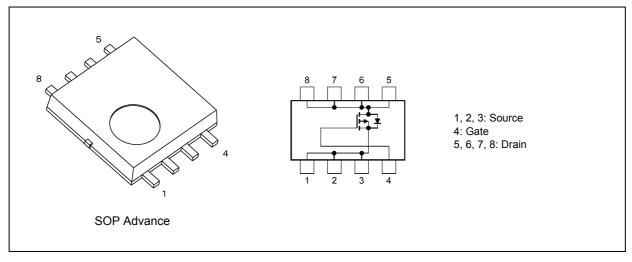
#### 1. Applications

- Lithium-Ion Secondary Batteries
- Power Management Switches

#### 2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 2.4 \text{ m}\Omega$  (typ.) ( $V_{GS} = -10 \text{ V}$ )
- (3) Low leakage current:  $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -30 \ V)$
- (4) Enhancement mode:  $V_{th}$  = -0.8 to -2.0 V ( $V_{DS}$  = -10 V,  $I_D$  = -1 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	-30	V
Gate-source voltage			V <sub>GSS</sub>	-25/+20	
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	-45	A
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	-135	
Power dissipation	(Tc = 25 °C)		PD	45	w
Power dissipation	(t = 10 s)	(Note 2)	PD	2.8	w
Power dissipation	(t = 10 s)	(Note 3)	PD	1.6	W
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	263	mJ
Avalanche current			I <sub>AR</sub>	-45	A
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	1

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

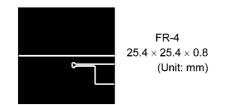
Characteri	Symbol	Max	Unit		
Channel-to-case thermal resistance	(Tc = 25 °C)		R <sub>th(ch-c)</sub>	2.78	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 2)	R <sub>th(ch-a)</sub>	44.6	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R <sub>th(ch-a)</sub>	78.1	°C/W

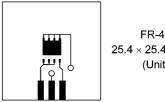
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V\_DD = -24 V, T\_ch = 25°C (initial), L = 0.1 mH, R\_G = 25  $\Omega,~I_{AR}$  = -45 A





FR-4  $25.4\times25.4\times0.8$ (Unit: mm)

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

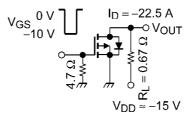
#### 6.1. Static Characteristics

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V	_	_	-10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-30	_	_	V
Drain-source breakdown voltage (Note 5)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 10 V	-21	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-0.8	—	-2.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -22.5 A		3.1	4.0	mΩ
		V <sub>GS</sub> = -10 V, I <sub>D</sub> = -22.5 A	_	2.4	3.0	

Note 5: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

#### 6.2. Dynamic Characteristics

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	7420	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	1180	_	
Output capacitance	C <sub>oss</sub>		_	1440	—	
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	_	10	—	ns
Switching time (turn-on time)	t <sub>on</sub>		_	18	_	
Switching time (fall time)	t <sub>f</sub>			262	_	
Switching time (turn-off time)	t <sub>off</sub>		_	762	_	



Duty  $\leq$  1%,  $t_W$  = 10  $\mu s$ 

#### Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics

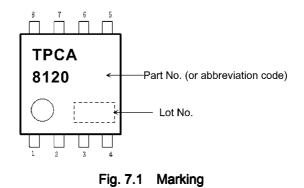
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx$ -24 V, $V_{GS}$ = -10 V, $I_D$ = -45 A	—	190	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	23	_	
Gate-drain charge	Q <sub>gd</sub>		_	47	_	

#### 6.4. Source-Drain Characteristics

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Pulsed reverse drain current	(Note 6)	I <sub>DRP</sub>	_	_	—	-135	Α
Diode forward voltage		$V_{DSF}$	I <sub>DR</sub> = -45 A, V <sub>GS</sub> = 0 V			1.2	V

Note 6: Ensure that the channel temperature does not exceed 150°C.

7. Marking



-6

-4

-32

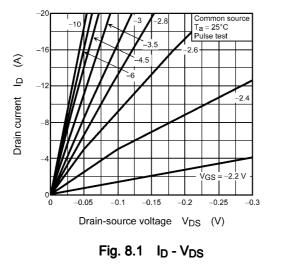
\_16

0**L** 0

€

Drain current I<sub>D</sub>

### 8. Characteristics Curves (Note)



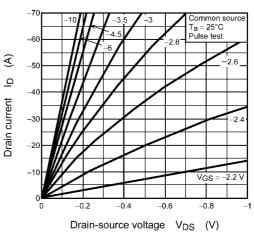


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

Common source Ta = 25°C

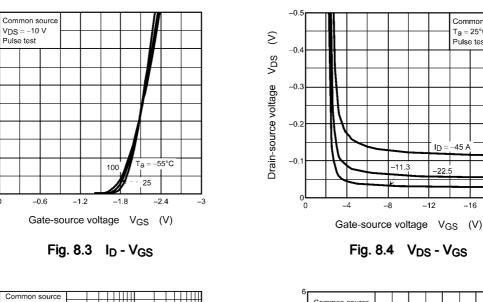
Pulse test

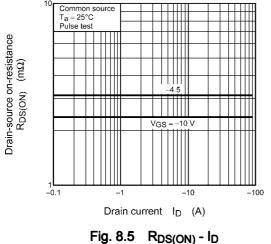
-45 / ID =

-16

-20

-12





Common source Pulse test Drain-source on-resistance  $R_{DS(ON)}$  (m $\Omega$ ) ı ب . 11.3, -22.5 -45 A VGS = -4.5 V 1.3, –22.5, -45 A ID, VGS . 10 V 0 -80 -40 0 40 80 120 160 Ambient temperature Ta (°C)

S

Gate threshold voltage

-1. < th

-1.

-0.8

-0.4

\_0 80–

3

2.5

0.5

0 0

40

(1)

(2)1.5

Ś

**Р** 

Drain power dissipation

Common source

-40

0

40

Ambient temperature Ta (°C) Fig. 8.9 V<sub>th</sub> - T<sub>a</sub>

> (1) Device mounted on a glass-epoxy board (a) (Note 2)

(2) Device mounted on a

10 s

80

Ambient temperature Ta (°C)

Fig. 8.11 P<sub>D</sub> - T<sub>a</sub>

(Guaranteed Maximum)

glass-epoxy board (b) (Note 3)

120

160

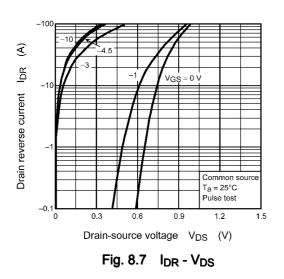
80

120

160

 $V_{DS} = -10 V$  $I_{D} = -1mA$ 

Pulse test



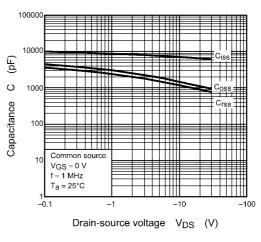


Fig. 8.8 Capacitance - V<sub>DS</sub>

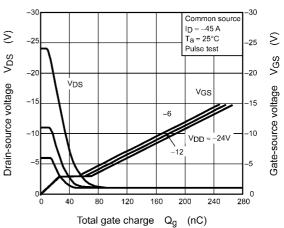
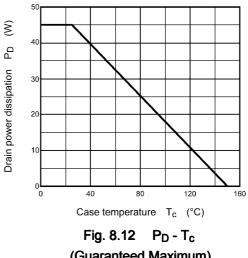
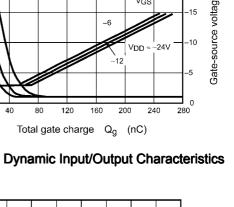
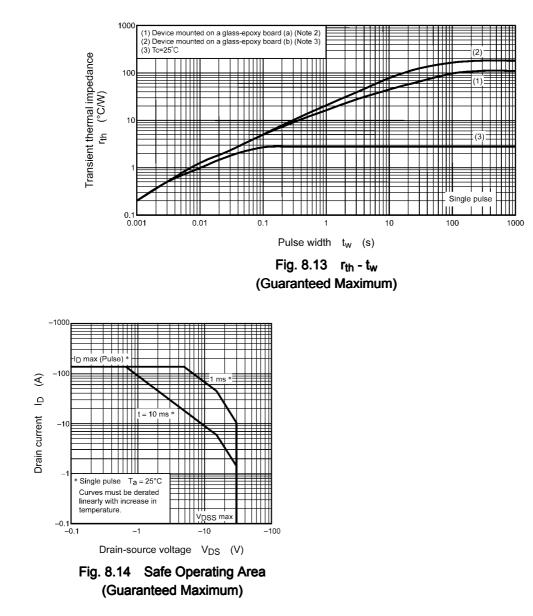


Fig. 8.10 Dynamic Input/Output Characteristics



(Guaranteed Maximum)



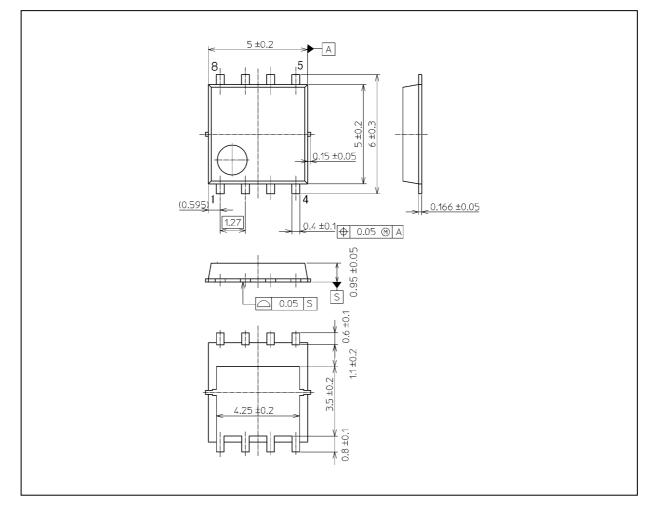


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### TPCA8120

#### Package Dimensions

Unit: mm



Weight: 0.069 g (typ.)

Package Name(s)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

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